## AMENDMENTS TO THE CLAIMS

Claim 1 (Previously Presented): A nitride semiconductor light emitting diode comprising:

an active layer comprising a nitride semiconductor; and

a reflecting mirror separated by a distance of approximately  $(k \cdot N2 + N4)/n$  from a center of the active layer, where

 $\lambda$  is the wavelength of light projected from the active layer,

 $\,$  n is the mean refractive index of an area between the active layer and the reflecting mirror, and

k is an integer.

Claim 2 (Original): A nitride semiconductor light emitting diode as set forth in Claim 1, wherein the reflecting mirror is also an electrode for supplying electric current to the active layer.

Claim 3 (Previously Presented): A nitride semiconductor light emitting diode as set forth in Claim 1, further comprising a convex lens on a side of the active layer opposite the reflecting mirror.

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Claim 4 (Previously Presented): A nitride semiconductor light emitting diode comprising:

a substrate;

an active layer comprising a nitride semiconductor on the substrate; and a reflecting mirror laminated above the active layer, the reflecting mirror being separated by a distance of approximately  $(k \cdot N/2 + N/4)/n$  from a center of the active layer, where

 $\lambda$  is the wavelength of light projected from the active layer,  $n \mbox{ is the mean refractive index of an area between the active layer and the } \\ reflecting mirror, and$ 

k is an integer.

Claims 5-8 (Canceled)

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Claim 9 (Previously Presented): A nitride semiconductor light emitting diode comprising:

a substrate;

a nitride semiconductor on the substrate,

where the nitride semiconductor is thick at a central portion thereof and thin at a peripheral portion thereof, and

where the nitride semiconductor has an active layer in the thick central portion .
thereof;

a first electrode on an upper face of the thick central portion; and a second electrode on an upper face of the thin peripheral portion, wherein the nitride semiconductor light emitting diode further comprises a reflecting mirror formed above the active layer of the thick central portion, the reflecting mirror being separated by a distance of approximately  $(k \cdot N2 + N4)/n$  from a center of the active layer, where

 $\lambda$  is the wavelength of light projected from the active layer,  $n \ \ is \ the \ mean \ refractive \ index \ of \ an \ area \ between \ the \ active \ layer \ and \ the$  reflecting mirror, and

k is an integer.

Claims 10-12 (Canceled)